



**Features**

- n Interdigitated amplifying gates
- n Fast turn-on and high di/dt
- n Low switching losses

**Typical Applications**

- n Inductive heating
- n Self-commutated inverters

**Part No. Y89KFG-KT84c(d)T**

<b>I<sub>T(AV)</sub></b>	<b>3800A</b>
<b>V<sub>DRM</sub></b>	<b>2000~3000V</b>
<b>V<sub>RRM</sub></b>	<b>1000~2500V</b>
<b>t<sub>q</sub></b>	<b>30-100 μs</b>

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T <sub>j</sub> (°C)	VALUE			UNIT	
					Min	Type	Max		
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T <sub>C</sub> =55°C	125			3800	A	
V <sub>DRM</sub>	Repetitive peak off-state voltage	tp=10ms		125	2000		3000	V	
V <sub>RRM</sub>	Repetitive peak reverse voltage		125	1000		2500	V		
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>		125			250	mA	
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave		125			46	kA	
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>					10580	A <sup>2</sup> s*10 <sup>3</sup>	
V <sub>TO</sub>	Threshold voltage			125			1.32	V	
r <sub>T</sub>	On-state slope resistance						0.14	mΩ	
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =5000A, F=70kN	30μs ≤ tq ≤ 45μs	25			2.60	V	
			46μs ≤ tq ≤ 70μs				2.00	V	
			71μs ≤ tq ≤ 100μs				1.80	V	
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>		125			1000	V/μs	
di/dt	Critical rate of rise of on-state current (Non-repetitive)	V <sub>DM</sub> = 67%V <sub>DRM</sub> , to4000A Gate pulse t <sub>r</sub> ≤ 0.5μs I <sub>GM</sub> =1.5A		125			1200	A/μs	
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =2000A, tp=4000μs, di/dt=-20A/μs, V <sub>R</sub> =100V		125		2100		μC	
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =2000A, tp=4000μs, V <sub>R</sub> =100V dv/dt=30V/μs, di/dt=-20A/μs		125	30		100	μs	
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A		25			40	450	mA
V <sub>GT</sub>	Gate trigger voltage					0.9		4.5	V
I <sub>H</sub>	Holding current					20		1000	mA
I <sub>L</sub>	Latching current							1500	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>		125			0.3	V	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine- double side cooled Clamping force 70 kN					0.007	°C /W	
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink						0.002		
F <sub>m</sub>	Mounting force				63		84	kN	
T <sub>vj</sub>	Junction temperature				-40		125	°C	
T <sub>stg</sub>	Stored temperature				-40		140	°C	
W <sub>t</sub>	Weight					1390		g	
Outline	KT84cT								

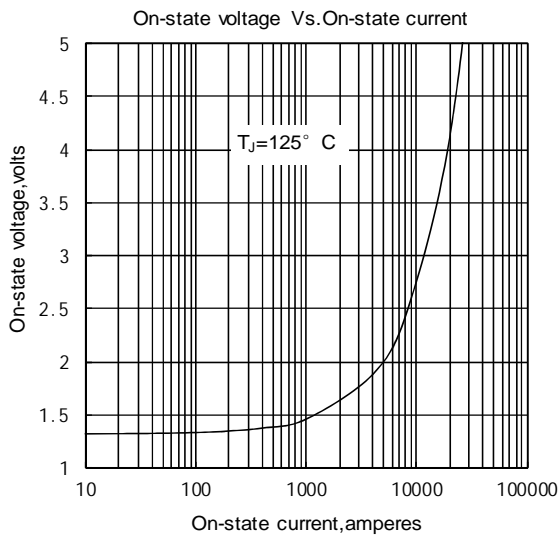


Fig.1

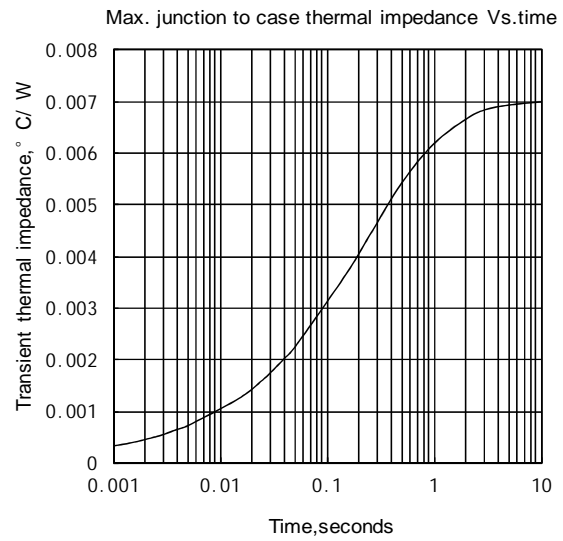


Fig.2

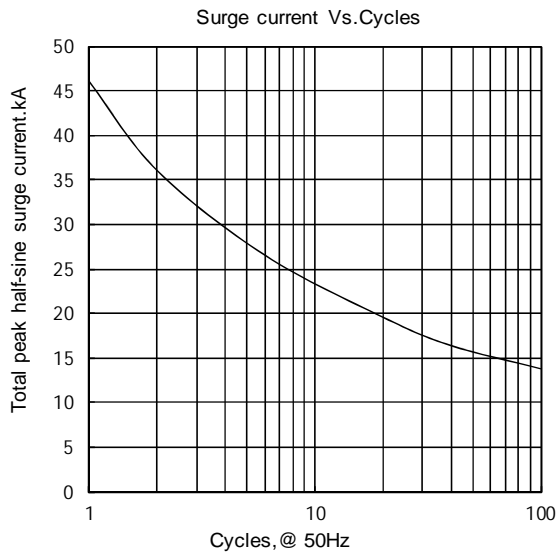


Fig.3

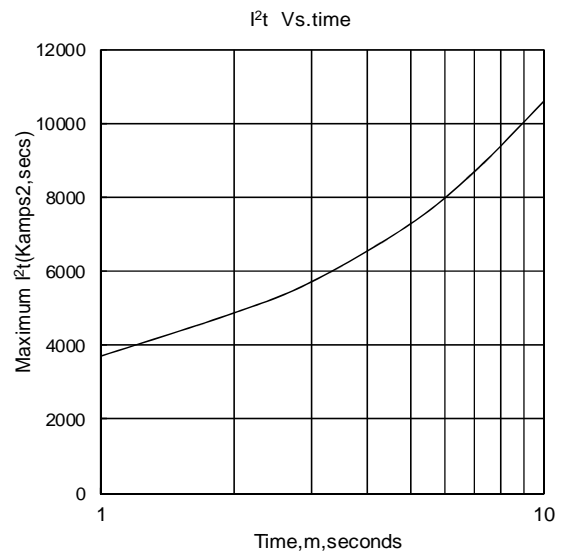


Fig.4

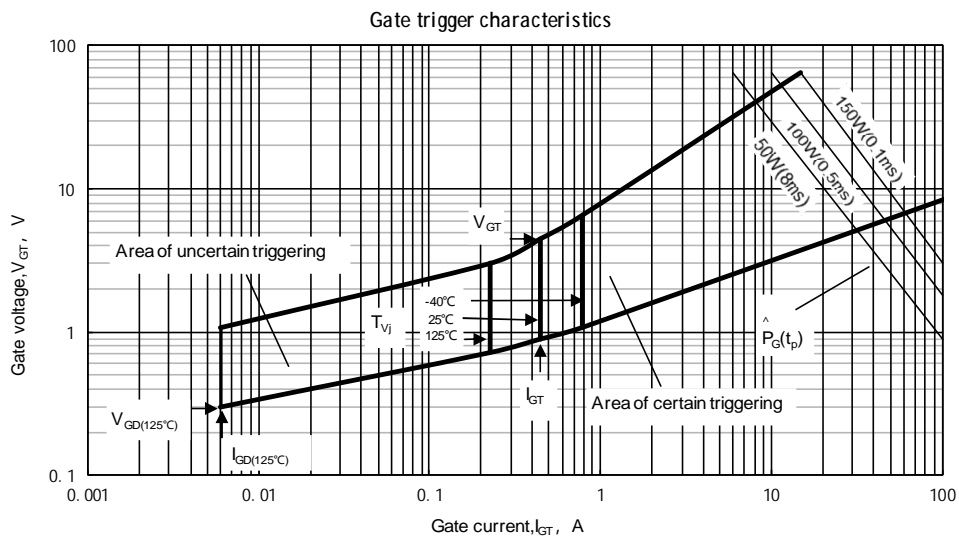
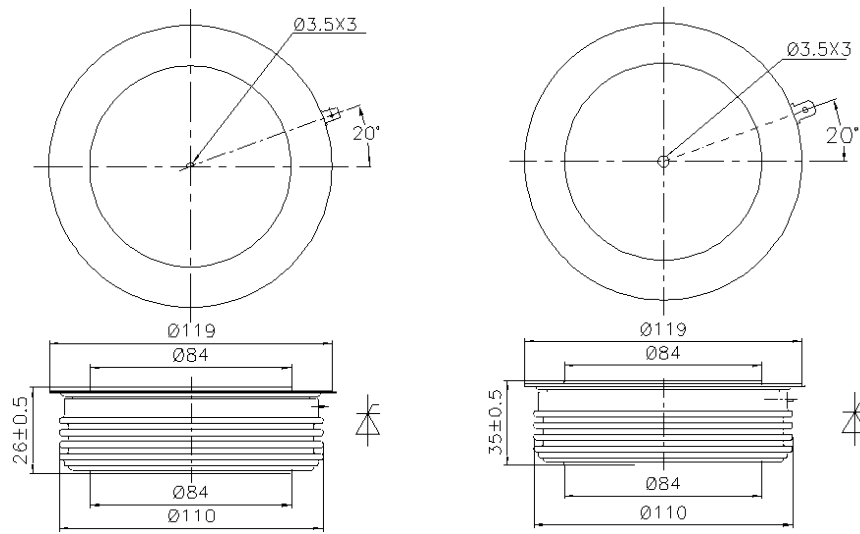


Fig.5

Outline:



TECHSEM reserves the right to change specifications without notice.